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[JP/JP]; c/o Semiconductor Energy Laboratory Co., Ltd.,  
398, Hase, Atsugi-shi, Kanagawa 2430036 (JP). SEO,  
Satoshi [JP/JP]; c/o Semiconductor Energy Laboratory  
Co., Ltd., 398, Hase, Atsugi-shi, Kanagawa 2430036 (JP).

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(71) Applicant (for all designated States except US): **SEMI-  
CONDUCTOR ENERGY LABORATORY CO., LTD.**  
[JP/JP]; 398, Hase, Atsugi-shi, Kanagawa 2430036 (JP).

(72) Inventors; and

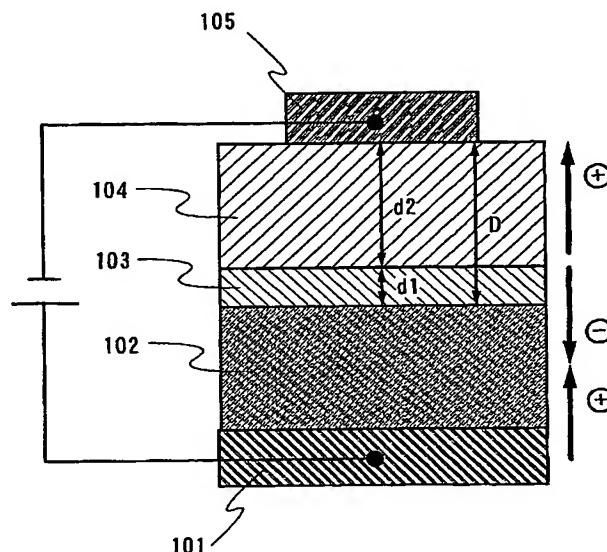
(75) Inventors/Applicants (for US only): **KUMAKI, Daisuke**

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(54) Title: **LIGHT-EMITTING ELEMENT**



(57) Abstract: In the present invention, a light-emitting element operating at low driving voltage, consuming low power, emitting light with good color purity and manufactured in high yields can be obtained. A light-emitting element is disclosed with a configuration composed of a first layer containing a light-emitting material, a second layer, a third layer are formed sequentially over an anode to be interposed between the anode and a cathode in such a way that the third layer is formed to be in contact with the cathode. The second layer is made from n-type semiconductor, a mixture including that, or a mixture of an organic compound having a carrier transporting property and a material having a high electron donor property. The third layer is made from p-type semiconductor, a mixture including that, or a mixture of an organic compound having a carrier transporting property and a material having a high electron acceptor property.

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